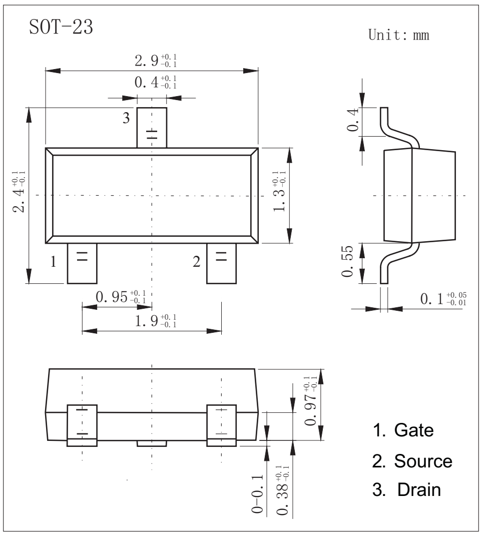
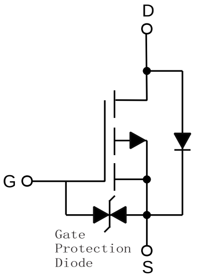
P-Channel MOSFET
BSS84K

Features

- V_{DS} (V) = -50V
- I_D = -130 mA
- $R_{DS(ON)} < 10\Omega$ (V_{GS} = -5V)
- ESD Protected 2KV HBM





Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	±20	
Continuous Drain Current	I_D	-130	mA
Pulsed Drain Current (tp≤10μs)	I_{DM}	-520	
Power Dissipation	P_D	225	mW
Thermal Resistance.Junction- to-Ambient	R_{thJA}	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

Marking

Marking	PD*

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■ Typical Characterisitics

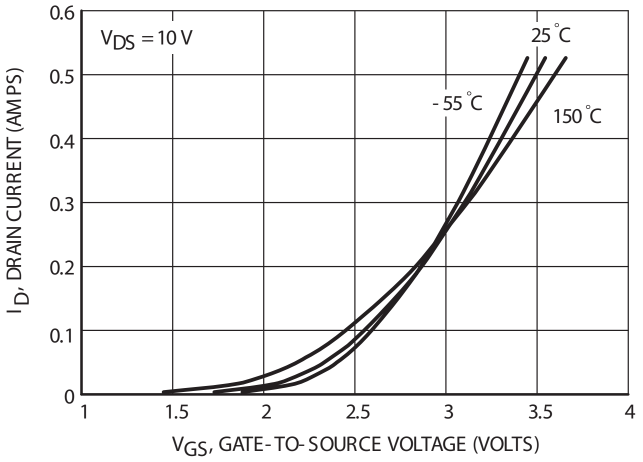

FIG1. Transfer Characteristics

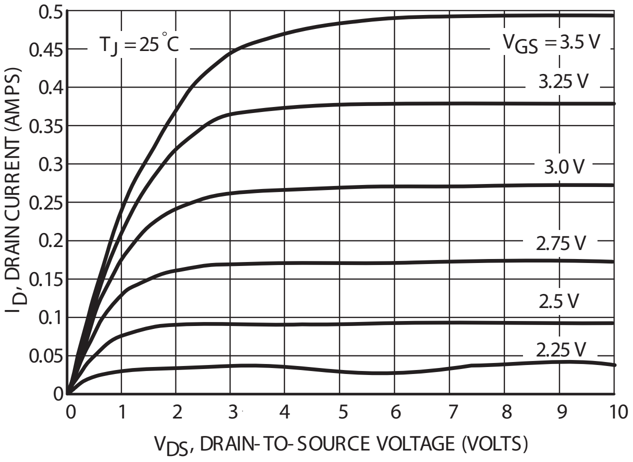

FIG2. On-Region Characteristics

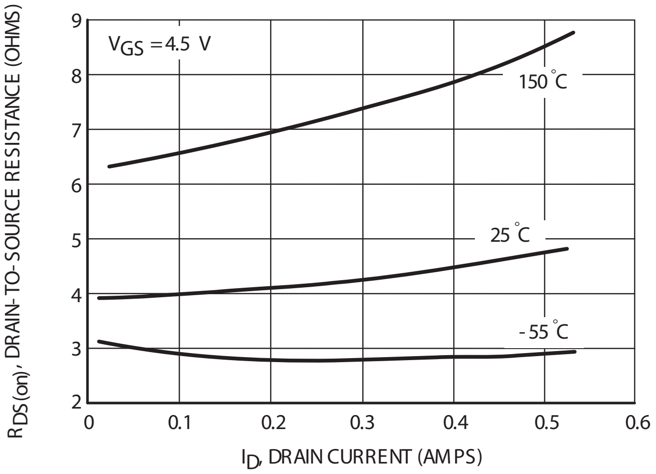

FIG3. On-Resistance versus Drain Current

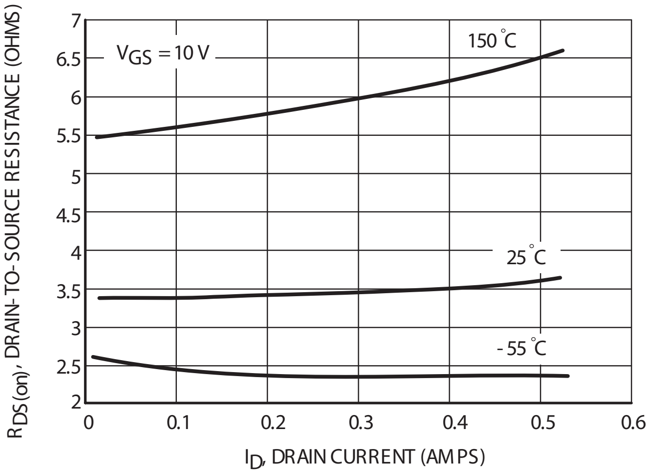

FIG4. On-Resistance versus Drain Current

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■ Typical Characterisitics

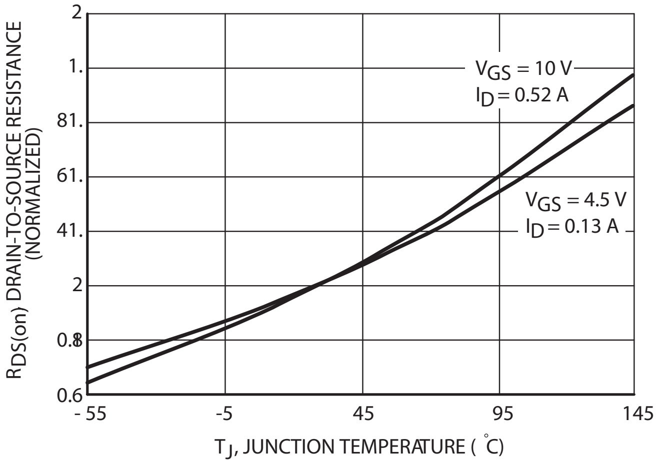

FIG5. On-Resistance Variation with Temperature

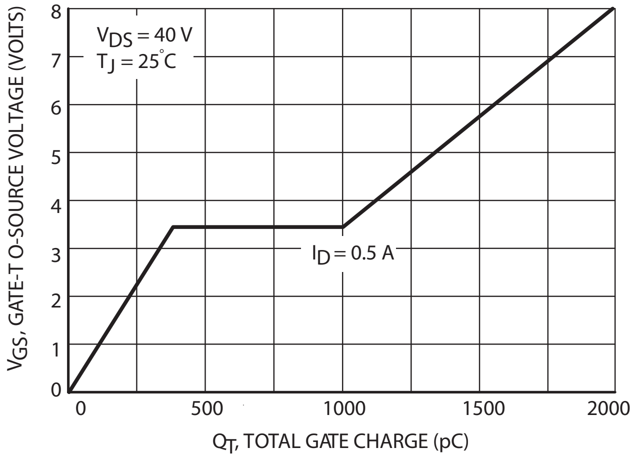

FIG6. Gate Charge

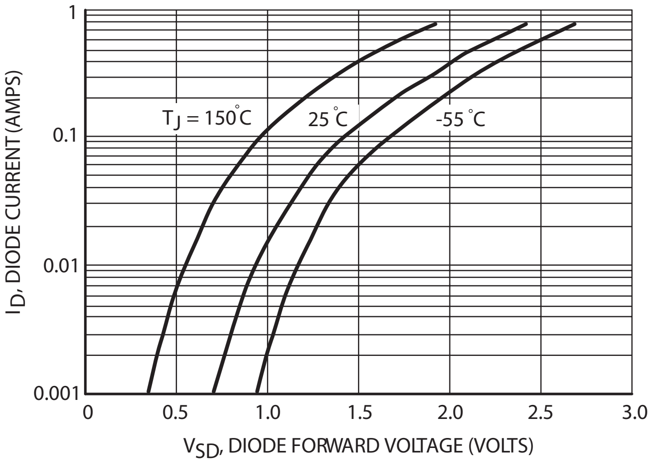

FIG7. Body Diode Forward Voltage